

# 2N5684 (PNP), 2N5686 (NPN)

## High-Current Complementary Silicon Power Transistors

These packages are designed for use in high-power amplifier and switching circuit applications.

### Features

- High Current Capability -  $I_C$  Continuous = 50 Amperes
- DC Current Gain -  $h_{FE} = 15 - 60 @ I_C = 25 \text{ Adc}$
- Low Collector-Emitter Saturation Voltage -  
 $V_{CE(sat)} = 1.0 \text{ Vdc (Max) @ } I_C = 25 \text{ Adc}$
- Pb-Free Packages are Available\*

### MAXIMUM RATINGS (Note 1)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	80	Vdc
Collector-Base Voltage	$V_{CB}$	80	Vdc
Emitter-Base Voltage	$V_{EB}$	5.0	Vdc
Collector Current - Continuous	$I_C$	50	Adc
Base Current	$I_B$	15	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	300 1.715	mW mW/ $^\circ\text{C}$
Operating and Storage Temperature Range	$T_J, T_{stg}$	-65 to +200	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$\theta_{JC}$	0.584	$^\circ\text{C/W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Indicates JEDEC Registered Data.

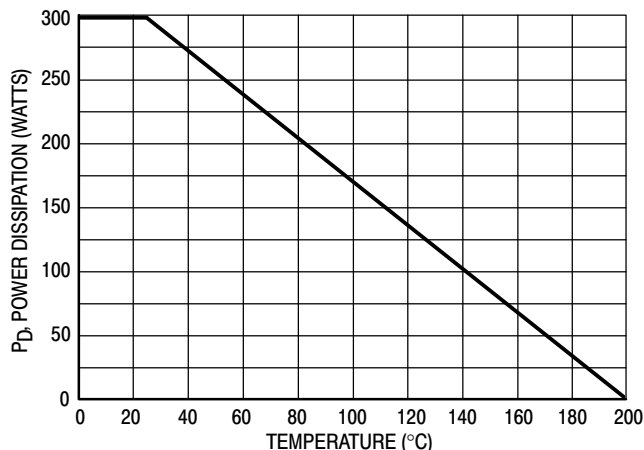


Figure 1. Power Derating

Safe Area Curves are indicated by Figure 5. All limits are applicable and must be observed.

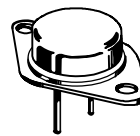


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## 50 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 60-80 VOLTS, 300 WATTS

### MARKING DIAGRAM



TO-204 (TO-3)  
CASE 197A  
STYLE 1

- 2N568x = Device Code  
x = 4 or 6  
G = Pb-Free Package  
A = Location Code  
YY = Year  
WW = Work Week  
MEX = Country of Origin

### ORDERING INFORMATION

Device	Package	Shipping
2N5684G	TO-3 (Pb-Free)	100 Units/Tray
2N5686	TO-3	100 Units/Tray
2N5686G	TO-3 (Pb-Free)	100 Units/Tray

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## 2N5684 (PNP), 2N5686 (NPN)

### ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted) (Note 2)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Sustaining Voltage (Note 3)	$V_{CEO(sus)}$	80	-	Vdc
Collector Cutoff Current	$I_{CEO}$	-	1.0	mAdc
Collector Cutoff Current	$I_{CEX}$	-	2.0	mAdc
		-	10	
		-	10	
Collector Cutoff Current	$I_{CBO}$	-	2.0	mAdc
Emitter Cutoff Current	$I_{EBO}$	-	5.0	mAdc

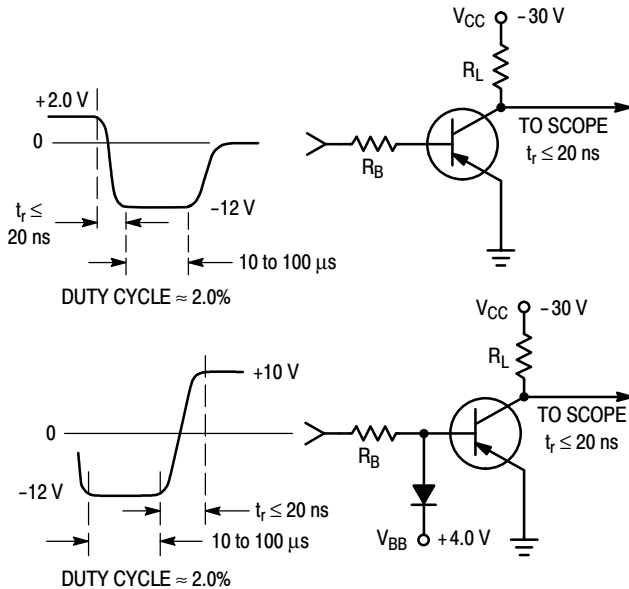
### ON CHARACTERISTICS

DC Current Gain (Note 3)	$h_{FE}$	15	60	-
		5.0	-	
Collector-Emitter Saturation Voltage (Note 3)	$V_{CE(sat)}$	-	1.0	Vdc
		-	5.0	
Base-Emitter Saturation Voltage (Note 2)	$V_{BE(sat)}$	-	2.0	Vdc
Base-Emitter On Voltage (Note 2)	$V_{BE(on)}$	-	2.0	Vdc

### DYNAMIC CHARACTERISTICS

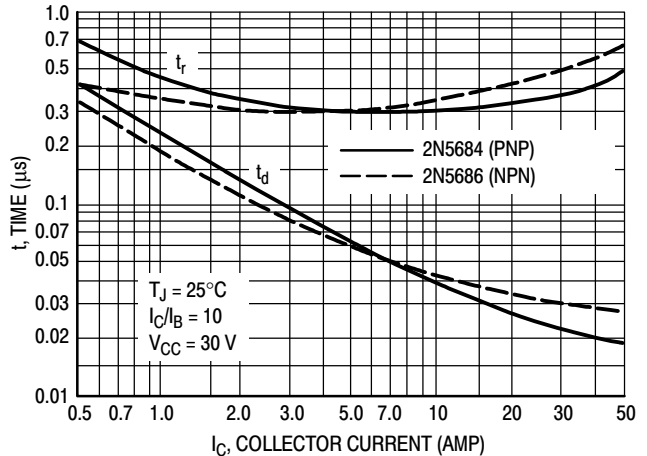
Current-Gain - Bandwidth Product	$f_T$	2.0	-	MHz
Output Capacitance	$C_{ob}$	-	2000	pF
		-	1200	
Small-Signal Current Gain	$h_{fe}$	15	-	

2. Indicates JEDEC Registered Data.  
 3. Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .



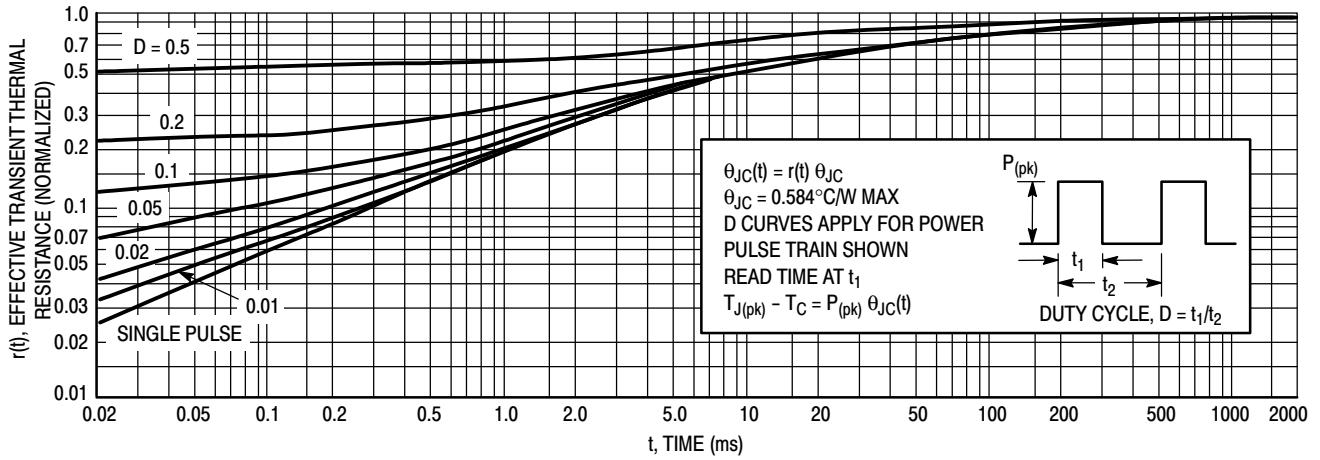
FOR CURVES OF FIGURES 3 & 6,  $R_B$  &  $R_L$  ARE VARIED.  
 INPUT LEVELS ARE APPROXIMATELY AS SHOWN.  
 FOR NPN CIRCUITS, REVERSE ALL POLARITIES.

**Figure 2. Switching Time Test Circuit**

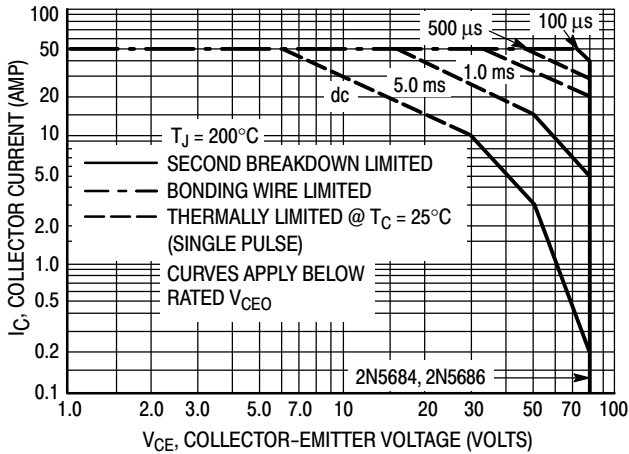


**Figure 3. Turn-On Time**

## 2N5684 (PNP), 2N5686 (NPN)



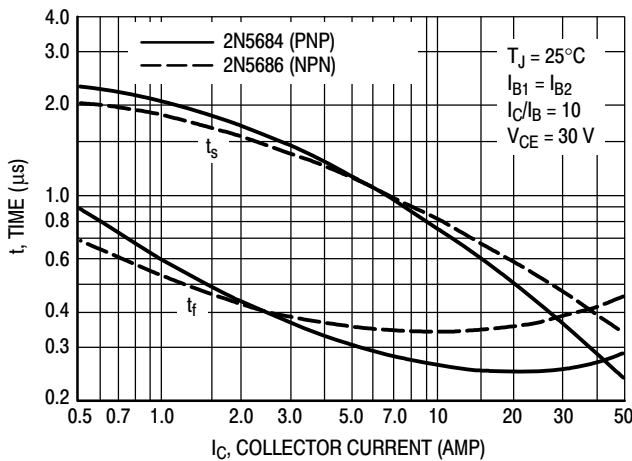
**Figure 4. Thermal Response**



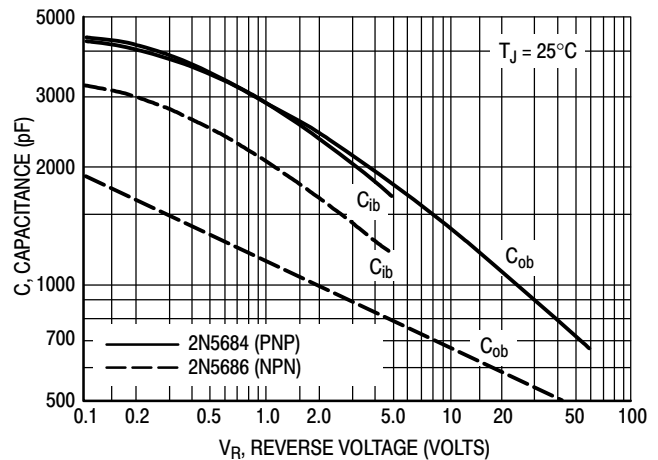
**Figure 5. Active-Region Safe Operating Area**

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on  $T_{J(pk)} = 200^{\circ}\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 200^{\circ}\text{C}$ .  $T_{J(pk)}$  may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.



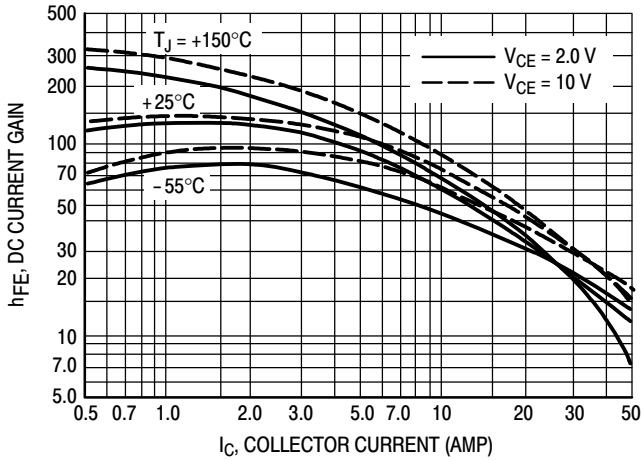
**Figure 6. Turn-Off Time**



**Figure 7. Capacitance**

# 2N5684 (PNP), 2N5686 (NPN)

**PNP**  
**2N5684**



**NPN**  
**2N5686**

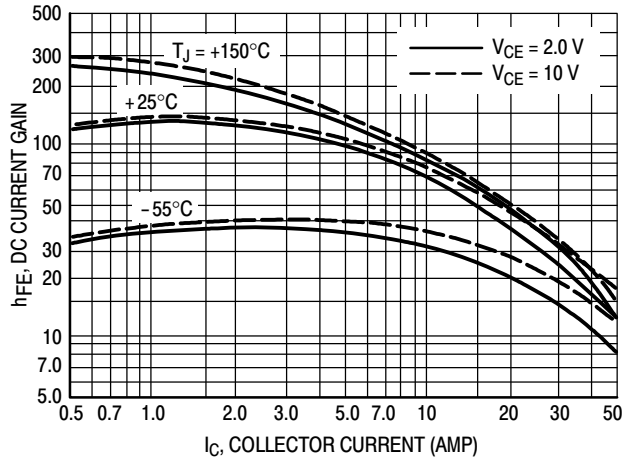


Figure 8. DC Current Gain

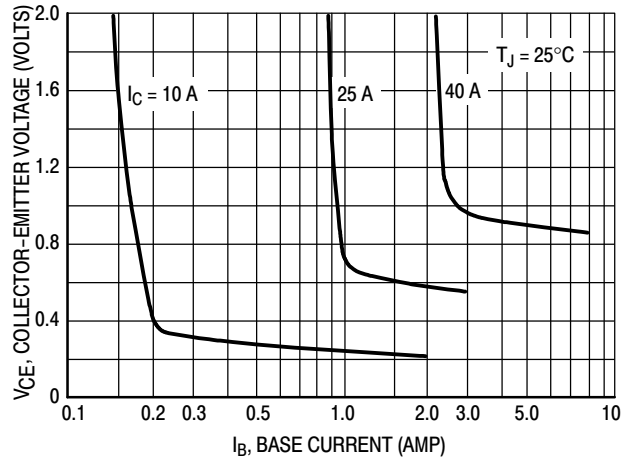
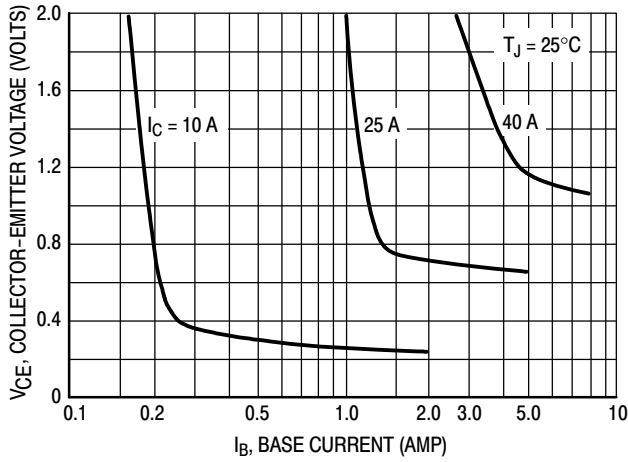


Figure 9. Collector Saturation Region

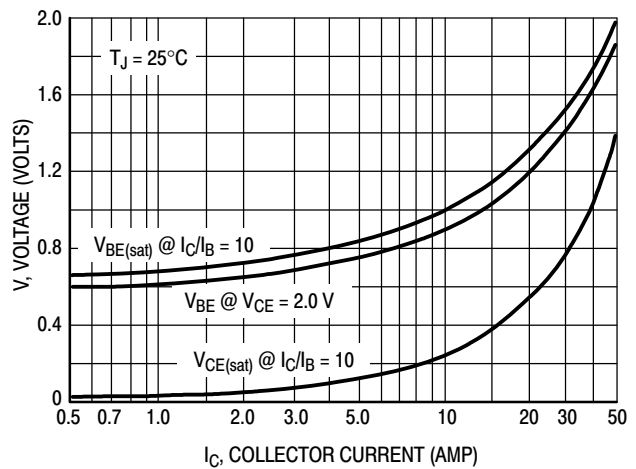
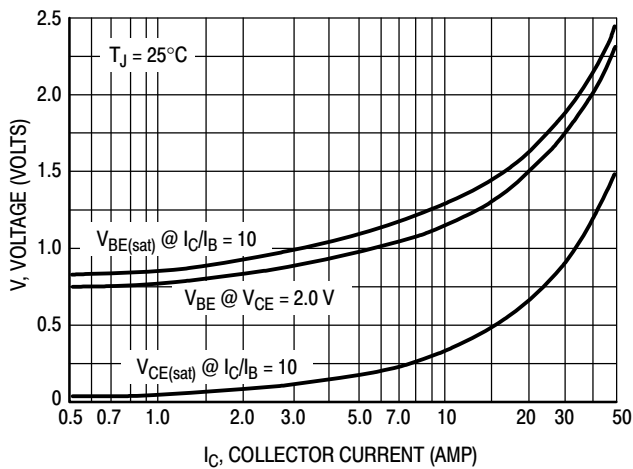
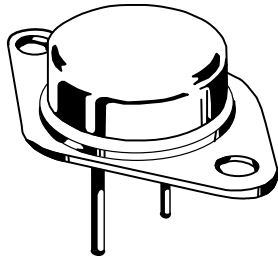


Figure 10. "On" Voltages

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

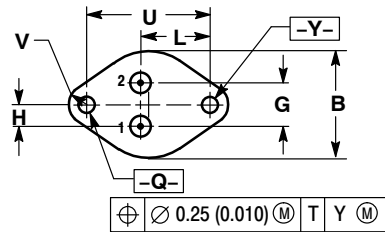
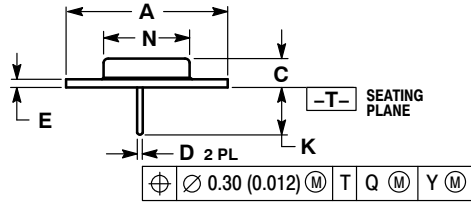
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TO-204 (TO-3)  
CASE 197A-05  
ISSUE K

DATE 21 FEB 2000

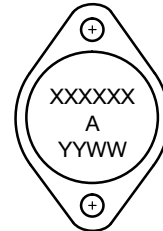
SCALE 1:1



- NOTES:  
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.530 REF		38.86 REF	
B	0.990	1.050	25.15	26.67
C	0.250	0.335	6.35	8.51
D	0.057	0.063	1.45	1.60
E	0.060	0.070	1.53	1.77
G	0.430 BSC		10.92 BSC	
H	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N	0.760	0.830	19.31	21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15 BSC	
V	0.131	0.188	3.33	4.77

### GENERIC MARKING DIAGRAM\*



XXXXXX = Specific Device Code  
A = Assembly Location  
YY = Year  
WW = Work Week

\*This information is generic. Please refer to device data sheet for actual part marking.

- STYLE 1: PIN 1. BASE  
2. EMITTER  
CASE: COLLECTOR
- STYLE 2: PIN 1. EMITTER  
2. BASE  
CASE: COLLECTOR
- STYLE 3: PIN 1. GATE  
2. SOURCE  
CASE: DRAIN
- STYLE 4: PIN 1. ANODE = 1  
2. ANODE = 2  
CASE: CATHODES

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STATUS:	ON SEMICONDUCTOR STANDARD	
NEW STANDARD:		
DESCRIPTION:	TO-204 (TO-3)	PAGE 1 OF 2



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